## VS-U5FX120FA120

### **Vishay Semiconductors**





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SO	1-227

PRIMARY CHARACTERISTICS							
V <sub>R</sub>	1200 V						
V <sub>F</sub> (typical) at 60 A, per diode	2.65 V						
t <sub>rr</sub> (typical) at 60 A, per diode	46 ns						
$I_{F(DC)}$ per module at $T_C = 70 \text{ °C}$	120 A						
Package	SOT-227						
Circuit configuration	Two separate diodes, parallel pin-out						

#### FEATURES

- Hyperfast and optimized Q<sub>rr</sub>
- Best in class forward voltage drop and switching losses trade off



- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Electrically isolated base plate
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- Designed and qualified for industrial level
- UL pending
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **DESCRIPTION / APPLICATIONS**

Featuring a unique combination of low conduction and switching losses, the VS-U5FX120FA120 is the right choice for high frequency converters, both soft switched / resonant. The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters, and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Cathode to anode voltage	V <sub>R</sub>		1200	V		
Continuous forward current per diode	I <sub>F</sub>	T <sub>C</sub> = 70 °C	60	۸		
Single pulse forward current per diode	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	385	A		
Maximum power dissipation per module	PD	T <sub>C</sub> = 70 °C	304	W		
RMS isolation voltage	V <sub>ISOL</sub>	Any terminal to case, t = 1 min	2500	V		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25$ °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA	1200	-	-	
Forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 60 A	-	2.75	3.33	V
		I <sub>F</sub> = 60 A, T <sub>J</sub> = 150 °C	-	2.15	-	
		V <sub>R</sub> = 1200 V	-	0.6	80	
Reverse leakage current	I <sub>RM</sub>	T <sub>J</sub> = 125 °C, V <sub>R</sub> = 1200 V	-	62	-	μA
		T <sub>J</sub> = 150 °C, V <sub>R</sub> = 1200 V	-	220	-	

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DYNAMIC RECOVERY CHARACTERISTICS (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Poverse receiven time	+	T <sub>J</sub> = 25 °C		-	46	-	20
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	91	-	ns
Dools recovery ourrent		$T_J = 25 \degree C$ $I_F =$	I <sub>F</sub> = 60 A, di <sub>F</sub> /dt = 1000 A/μs, V <sub>R</sub> = 800 V	-	24	-	^
Peak recovery current	IRRM	T <sub>J</sub> = 125 °C		-	42	-	A
	â	T <sub>J</sub> = 25 °C		-	1.2	-	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	3.5	-	μC
Junction capacitance	CT	V <sub>R</sub> = 1200 V		-	23	-	pF

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance junction to case, per diode	P		-	-	0.69	
Thermal resistance junction to case, per module	R <sub>thJC</sub>		-	-	0.345	°C/W
Thermal resistance case to heatsink, per module	R <sub>thCS</sub>	Flat, greased surface	-	0.05	-	
Weight			-	30	-	g
		Torque per diode	-	-	1.1 (9.7)	Nm (lbf.in)
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style				SOT	Г-227	

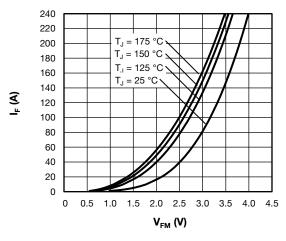


Fig. 1 - Typical Forward Voltage Drop Characteristics

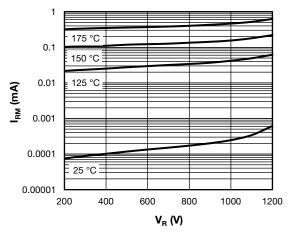


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



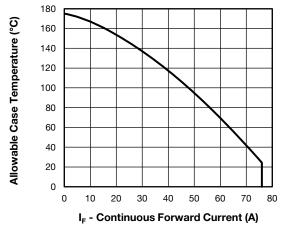


Fig. 3 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Diode)

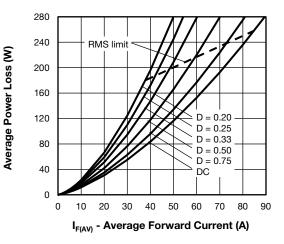


Fig. 4 - Average Power Loss vs. Average Forward Current

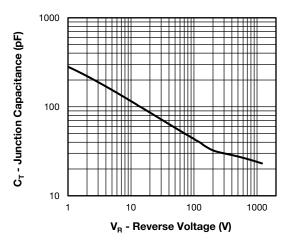
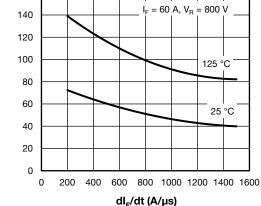


Fig. 5 - Junction Capacitance vs. Reverse Voltage

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VS-U5FX120FA120



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 $\mathbf{t}_{\mathrm{rr}}$  (ns)

Fig. 6 - Diode Reverse Recovery Time vs. dI<sub>F</sub>/dt

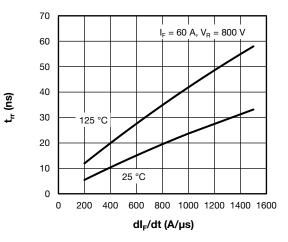


Fig. 7 - Diode Reverse Recovery Current vs. dl<sub>F</sub>/dt

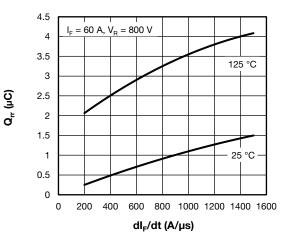


Fig. 8 - Diode Reverse Recovery Charge vs. dl<sub>F</sub>/dt

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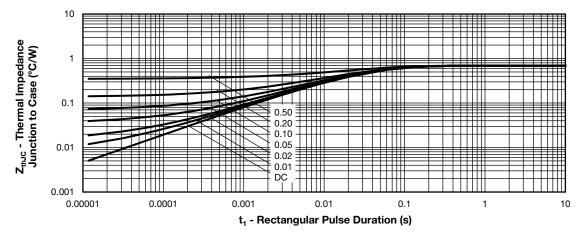


Fig. 9 - Maximum Thermal Impedance Junction to Case

### ORDERING INFORMATION TABLE

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SHAY

Device code	VS-	U5F	х	120	F	Α	120	
	1	2	3	4	5	6	7	
	1       -         2       -         3       -         4       -         5       -         6       -         7       -	- U5F - X = - Cur - F = - Pac	= Gen Hyperfa rent rati circuit c kage in	0	Pt <sup>®</sup> far D Pt <sup>®</sup> di module ation (tw	nily ode (120 = <sup>-</sup> vo sepa ?7 stanc	rate dio	odes, parallel pin-out) ulated base)

CIRCUIT CONFI	GURATION	
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two separate diodes, parallel pin-out	F	Lead Assignment

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95423				
Packaging information	www.vishay.com/doc?95425				

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